

General Purpose Transistors

PNP Silicon

FEATURE

- Simplifies Circuit Design.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

ORDERING INFORMATION

Device	Marking	Shipping
LMBT3906TT1G S-LMBT3906TT1G	2A 2A	4000/Tape & Reel
LMBT3906TT3G S-LMBT3906TT3G	2A 2A	10000/Tape & Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	- 40	Vdc
Collector–Base Voltage	V_{CBO}	- 40	Vdc
Emitter–Base Voltage	V_{EBO}	- 5.0	Vdc
Collector Current — Continuous	I_C	- 200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-4 Board(1) $T_A = 25^\circ\text{C}$	P_D	200	mW
Derate above 25°C		1.6	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	600	$^\circ\text{C}/\text{W}$
Total Device Dissipation FR-4 Board (2), $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	400	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

DEVICE MARKING

LMBT3906TT1G = 2A

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

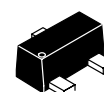
Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

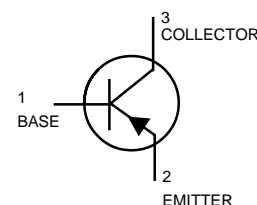
Collector–Emitter Breakdown Voltage (3) ($I_C = -1.0\text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	- 40	—	Vdc
Collector–Base Breakdown Voltage ($I_C = -10\ \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	- 40	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10\ \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	- 5.0	—	Vdc
Base Cutoff Current ($V_{CE} = -30\text{ Vdc}, V_{EB} = -3.0\text{ Vdc}$)	I_{BL}	—	- 50	nAdc
Collector Cutoff Current ($V_{CE} = -30\text{ Vdc}, V_{EB} = -3.0\text{ Vdc}$)	I_{CEX}	—	- 50	nAdc

1. FR-4 Minimum Pad.
2. FR-4 1.0 x 1.0 Inch Pad.
3. Pulse Width $\leq 300\ \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

LMBT3906TT1G
S-LMBT3906TT1G



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LMBT3906TT1G;S-LMBT3906TT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS (3)				
DC Current Gain ($I_C = -0.1 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$)	h_{FE}	60	—	—
($I_C = -1.0 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$)		80	—	
($I_C = -10 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$)		100	300	
($I_C = -50 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$)		60	—	
($I_C = -100 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$)		30	—	
Collector–Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc}$)	$V_{CE(sat)}$	—	-0.25	Vdc
($I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$)		—	-0.4	
Base–Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc}$)	$V_{BE(sat)}$	-0.65	-0.85	Vdc
($I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$)		—	-0.95	

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = -10 \text{ mAdc}, V_{CE} = -20 \text{ Vdc}, f = 100 \text{ MHz}$)	f_T	250	—	MHz
Output Capacitance ($V_{CB} = -5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	C_{obo}	—	4.5	pF
Input Capacitance ($V_{EB} = -0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz}$)	C_{ibo}	—	10	pF
Input Impedance ($V_{CE} = -10 \text{ Vdc}, I_C = -1.0 \text{ mAdc}, f = 1.0 \text{ kHz}$)	h_{ie}	2.0	12	k Ω
Voltage Feedback Ratio ($V_{CE} = -10 \text{ Vdc}, I_C = -1.0 \text{ mAdc}, f = 1.0 \text{ kHz}$)	h_{re}	0.1	10	$\times 10^{-4}$
Small–Signal Current Gain ($V_{CE} = -10 \text{ Vdc}, I_C = -1.0 \text{ mAdc}, f = 1.0 \text{ kHz}$)	h_{fe}	100	400	—
Output Admittance ($V_{CE} = -10 \text{ Vdc}, I_C = -1.0 \text{ mAdc}, f = 1.0 \text{ kHz}$)	* h_{oe}	3.0	60	μmhos
Noise Figure ($V_{CE} = -5.0 \text{ Vdc}, I_C = -100 \mu\text{Adc}, R_S = 1.0 \text{ k}\Omega, f = 1.0 \text{ kHz}$)	NF	—	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = -3.0 \text{ Vdc}, V_{BE} = 0.5 \text{ Vdc}, I_C = -10 \text{ mAdc}, I_{B1} = -1.0 \text{ mAdc})$	t_d	—	35	ns
Rise Time		t_d	—	35	
Storage Time	$(V_{CC} = -3.0 \text{ Vdc}, I_C = -10 \text{ mAdc}, I_{B1} = I_{B2} = -1.0 \text{ mAdc})$	t_s	—	225	ns
Fall Time		t_f	—	75	

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

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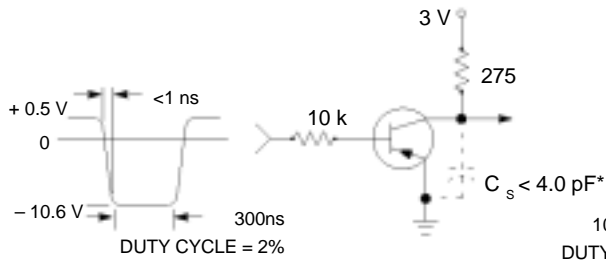


Figure 1. Delay and Rise Time
Equivalent Test Circuit

*Total shunt capacitance of test jig and connectors

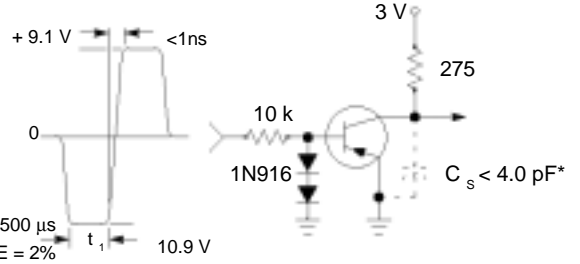


Figure 2. Storage and Fall Time
Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

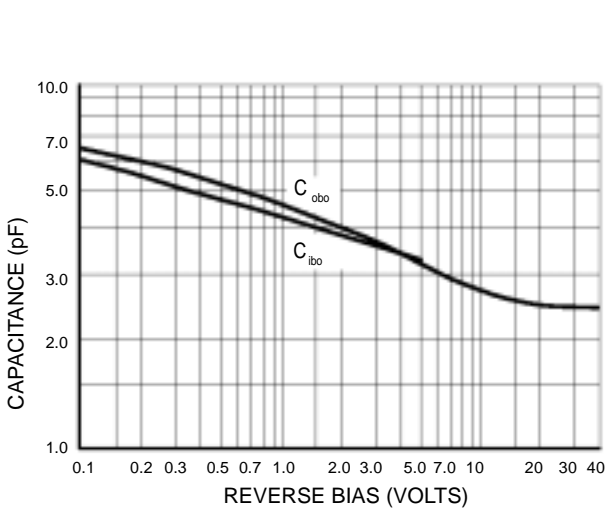


Figure 3. Capacitance

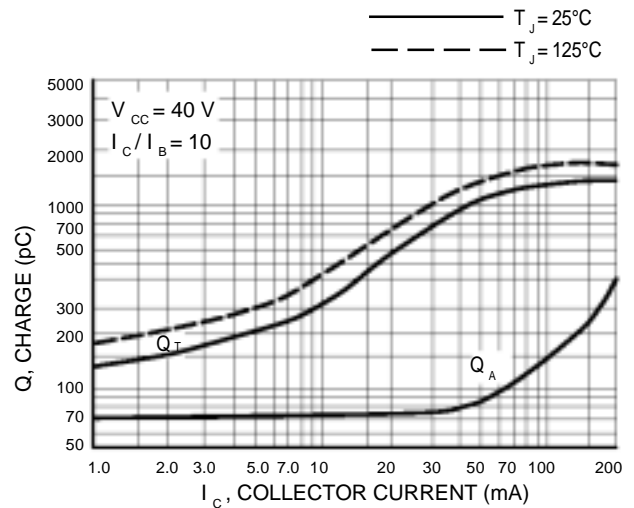


Figure 4. Charge Data

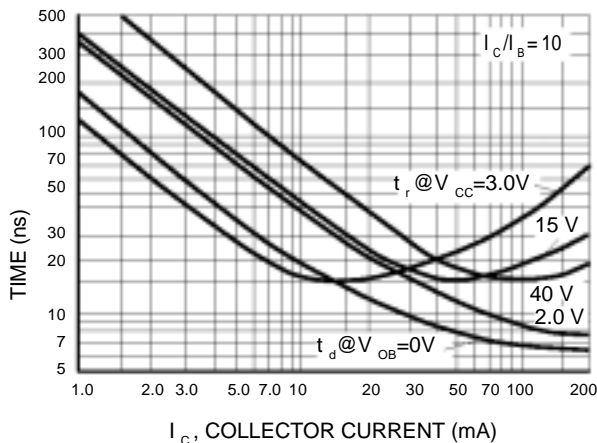


Figure 5. Turn-On Time

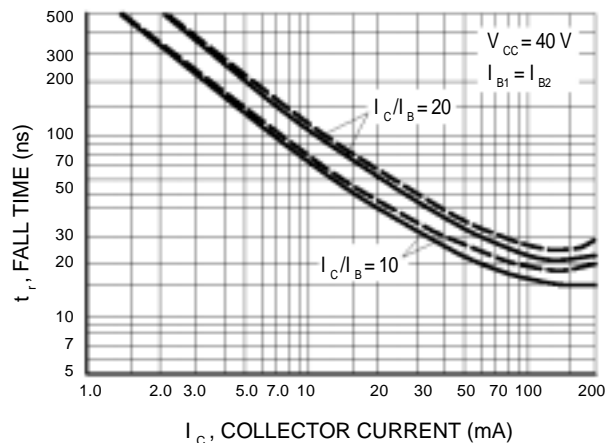


Figure 6. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

($V_{CE} = -5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

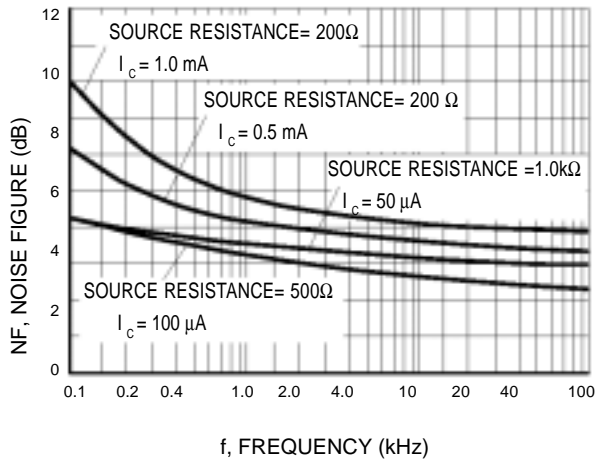


Figure 7. Noise Figure

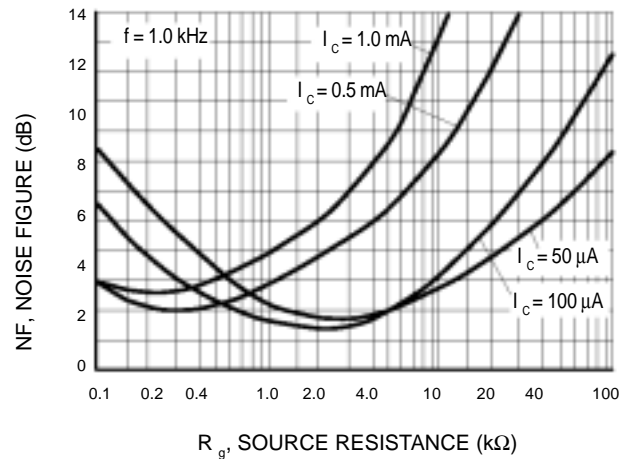


Figure 8. Noise Figure

h PARAMETERS

($V_{CE} = 10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

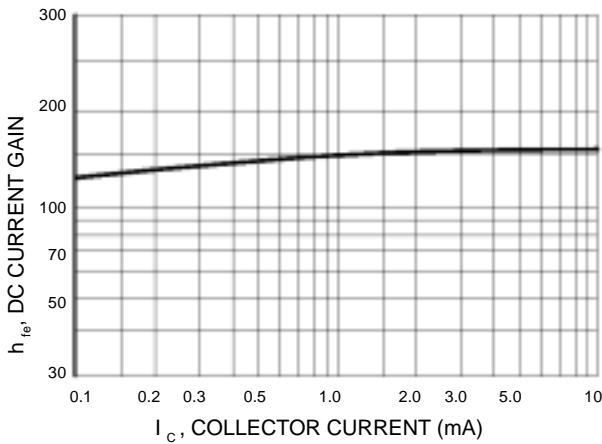


Figure 9. Current Gain

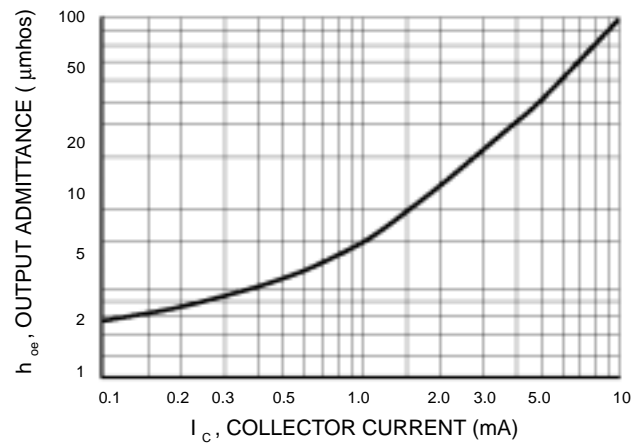


Figure 10. Output Admittance

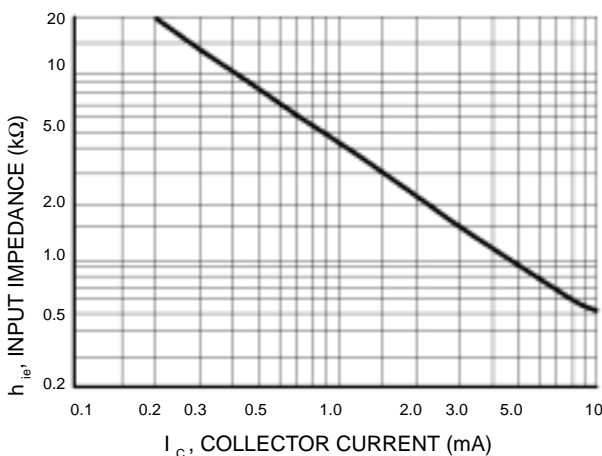


Figure 11. Input Impedance

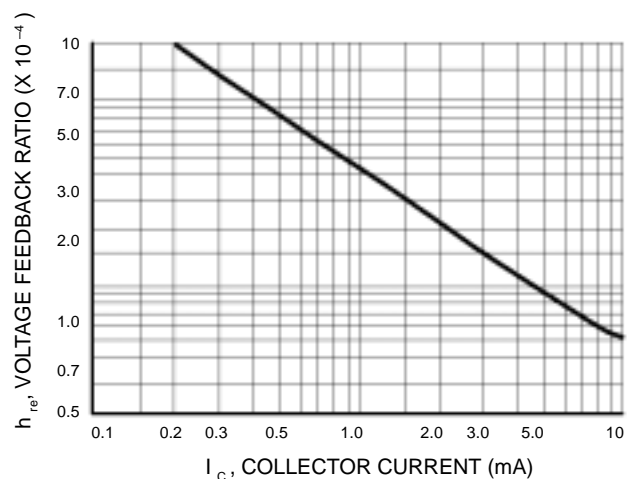


Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

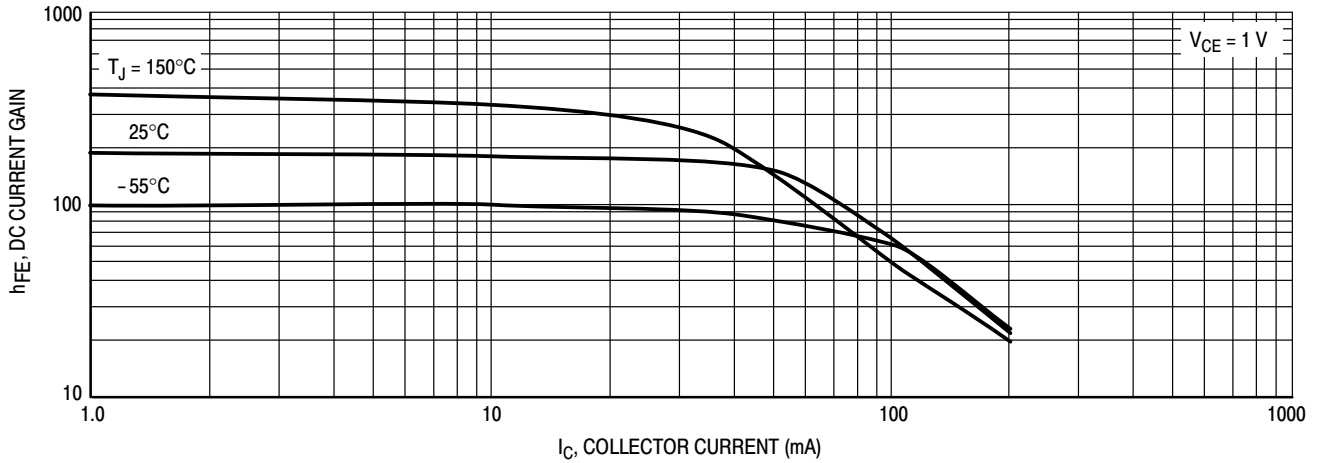


Figure 13. DC Current Gain

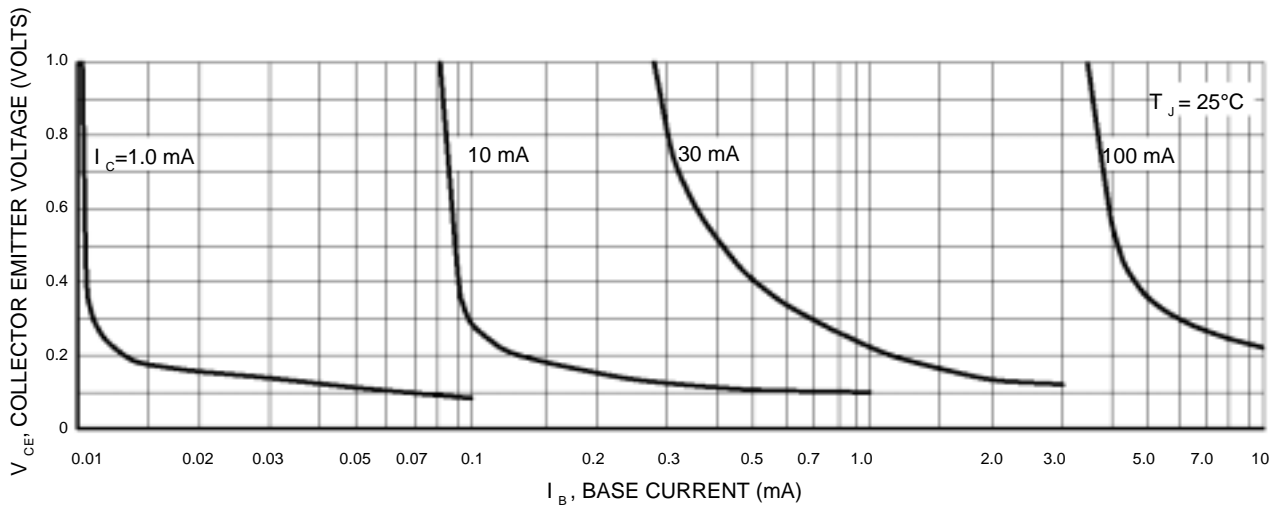


Figure 14. Collector Saturation Region

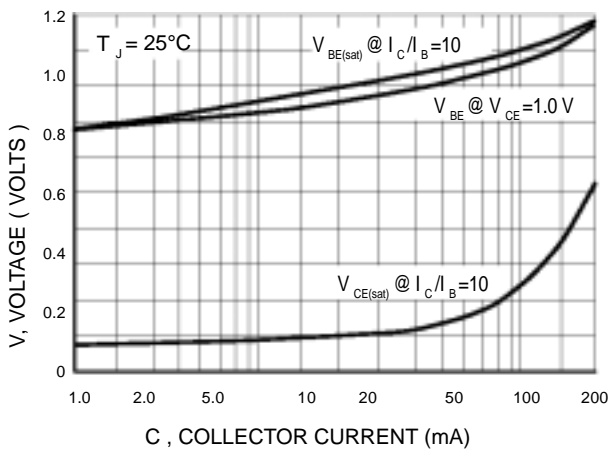


Figure 15. "ON" Voltages

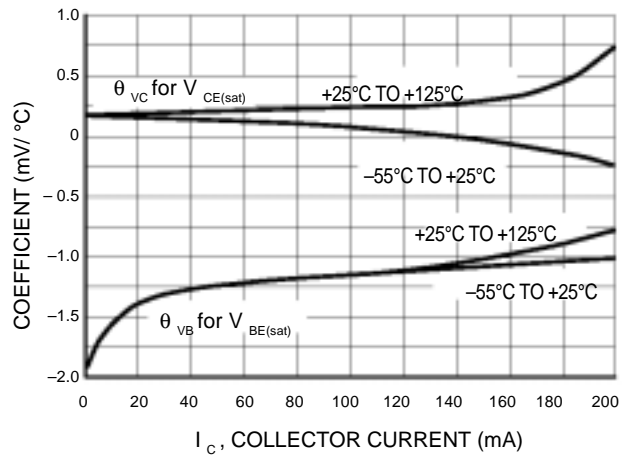
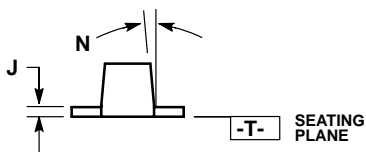
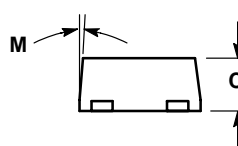
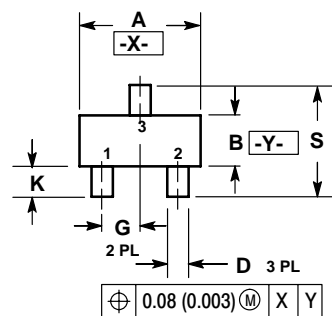


Figure 16. Temperature Coefficients

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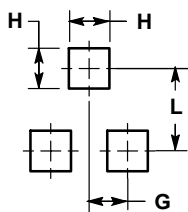
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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10 °	---	---	10 °
N	---	---	10 °	---	---	10 °
S	1.50	1.60	1.70	0.059	0.063	0.067



RECOMMENDED PATTERN OF SOLDER PADS

DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
- Before you use our Products for new Project, you are requested to carefully read this document and fully understand its contents. LRC shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any LRC's Products against warning, caution or note contained in this document.
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